

# 5N50

*Power MOSFET*

## 5A, 500V N-CHANNEL POWER MOSFET

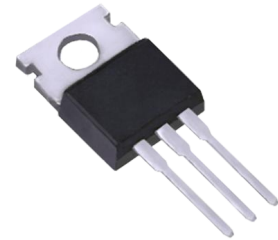
### ■ DESCRIPTION

The UTC **5N50** is an N-channel power MOSFET adopting UTC's advanced technology to provide customers with DMOS, planar stripe technology. This technology is designed to meet the requirements of the minimum on-state resistance and perfect switching performance. It also can withstand high energy pulse in the avalanche and communication mode.

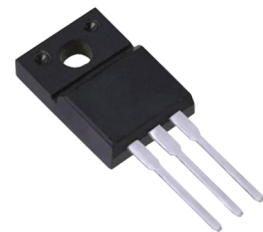
The UTC **5N50** can be used in applications, such as active power factor correction, high efficiency switched mode power supplies, electronic lamp ballasts based on half bridge topology.

### ■ FEATURES

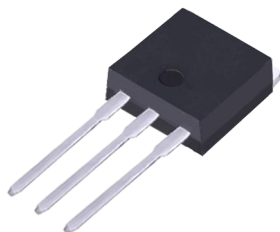
- \*  $R_{DS(ON)} < 1.4\Omega$  @  $V_{GS} = 10\text{ V}$ ,  $I_D = 2.5\text{ A}$
- \* 100% avalanche tested
- \* High switching speed



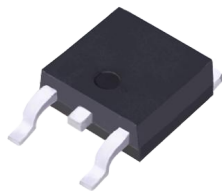
T0-220



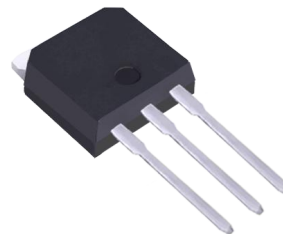
T0-220F



T0-262



T0-263



T0-251



T0-252

■ ABSOLUTE MAXIMUM RATINGS ( $T_c=25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	500	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Drain Current	Continuous	$I_D$	5	A
	Pulsed (Note 2)	$I_{DM}$	20	A
Avalanche Current (Note 2)		$I_{AR}$	5	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	300	mJ
	Repetitive (Note 2)	$E_{AR}$	7.3	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-262	$P_D$	125	W
	TO-220F/TO-220F1		38	W
	TO-252		54	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3.  $L = 21.5\text{mH}$ ,  $I_{AS} = 5\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 5\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-262/TO-220F	$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
	TO-220F1			
	TO-252			
Junction to Case	TO-262	$\theta_{JC}$	1	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1			
	TO-251			
			3.25	$^\circ\text{C}/\text{W}$
			2.13	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>							
Drain-Source Breakdown Voltage		$BV_{DSS}$	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	500			V
Breakdown Voltage Temperature Coefficient		$\Delta BV_{DSS}/\Delta T_J$	Reference to $25^\circ\text{C}$ , $I_D=250\mu\text{A}$		0.5		$\text{V}/^\circ\text{C}$
Drain-Source Leakage Current		$I_{DSS}$	$V_{DS}=500\text{V}$ , $V_{GS}=0\text{V}$			1	$\mu\text{A}$
			$V_{DS}=400\text{V}$ , $T_C=125^\circ\text{C}$			10	
Gate- Source Leakage Current	Forward	$I_{GSS}$	$V_{GS}=30\text{V}$ , $V_{DS}=0\text{V}$			100	nA
	Reverse		$V_{GS}=-30\text{V}$ , $V_{DS}=0\text{V}$			-100	nA
<b>ON CHARACTERISTICS</b>							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	$V_{GS}=10\text{V}$ , $I_D=2.5\text{A}$			1.4	$\Omega$
<b>DYNAMIC PARAMETERS</b>							
Input Capacitance		$C_{ISS}$	$V_{GS}=0\text{V}$ , $V_{DS}=25\text{V}$ , $f=1.0\text{MHz}$		535	625	pF
Output Capacitance		$C_{OSS}$			70	105	pF
Reverse Transfer Capacitance		$C_{RSS}$			17	20	pF
<b>SWITCHING PARAMETERS</b>							
Turn-ON Delay Time		$t_{D(ON)}$	$V_{DD}=30\text{V}$ , $I_D=0.5\text{A}$ , $R_G=25\Omega$ (Note 1, 2)		30	45	ns
Rise Time		$t_R$			50	70	ns
Turn-OFF Delay Time		$t_{D(OFF)}$			145	165	ns
Fall-Time		$t_F$			72	105	ns
Total Gate Charge		$Q_G$	$V_{GS}=10\text{V}$ , $V_{DS}=50\text{V}$ , $I_D=1.3\text{A}$ , $I_G=100\mu\text{A}$ (Note 1, 2)		20	24	nC
Gate to Source Charge		$Q_{GS}$			4		nC
Gate to Drain Charge		$Q_{GD}$			5		nC
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>							
Maximum Continuous Drain-Source Diode Forward Current		$I_S$				5	A
Maximum Pulsed Drain-Source Diode Forward Current		$I_{SM}$				20	A
Drain-Source Diode Forward Voltage		$V_{SD}$	$I_S=5\text{A}$ , $V_{GS}=0\text{V}$			1.4	V

Notes: 1. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$   
 2. Essentially independent of operating temperature

■ TYPICAL CHARACTERISTICS

